Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

3. Applications

- · Charging switch for portable devices
- DC-to-DC converters
- · Power management in battery-driven portables
- · Hard disk and computing power management

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	٧	
V_{GS}	gate-source voltage			-20	-	20	٧	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	13	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 25 \text{ °C}$		-	12	14.5	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 1 1 1 6	D I
2	D	drain		
3	G	gate	2 5	G LFA
4	S	source	3 8 4	s
5	D	drain	Transparent top view	017aaa253
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PMPB11EN	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220				

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB11EN	1C

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	13	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	9	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	5.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	34	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	2.2	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

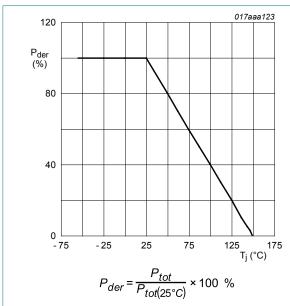


Fig. 1. Normalized total power dissipation as a function of junction temperature

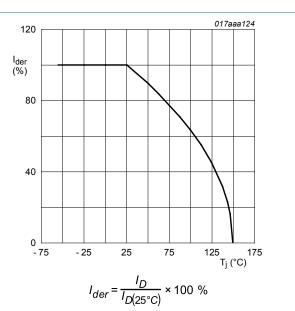
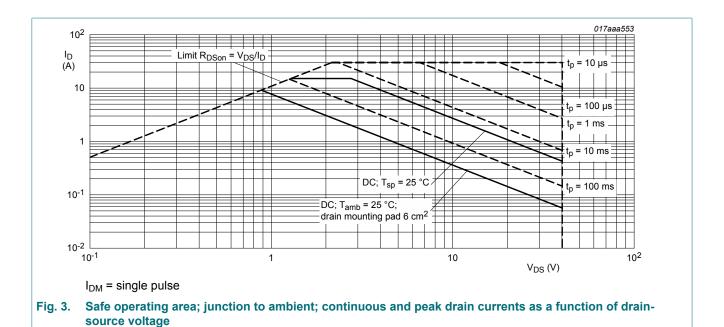


Fig. 2. Normalized continuous drain current as a function of junction temperature

3 / 15

30 V, N-channel Trench MOSFET



9. Thermal characteristics

Table 6. Thermal characteristics

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	235	270	K/W
	from junction to ambient		[2]	-	67	74	K/W
			[3]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm²
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², $t \le 5$ s

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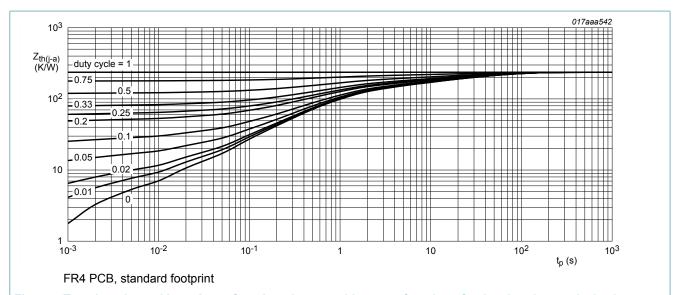


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

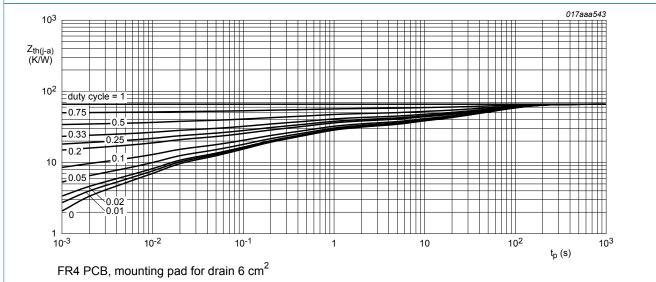


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	1	1.5	2	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	20	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 9 A; T _j = 25 °C	-	12	14.5	mΩ
	resistance	V _{GS} = 10 V; I _D = 9 A; T _j = 150 °C	-	18	20.5	mΩ
		V_{GS} = 4.5 V; I_D = 3.7 A; T_j = 25 °C	-	14	16.5	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	45	-	S
R_G	gate resistance	f = 1 MHz	-	1.6	-	Ω
Dynamic ch	naracteristics		•			·
Q _{G(tot)}	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 6 \text{ A}; V_{GS} = 10 \text{ V};$	-	13.7	20.6	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.73	-	nC
Q_{GD}	gate-drain charge		-	1.71	-	nC
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	840	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	155	-	pF
C _{rss}	reverse transfer capacitance		-	65	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 5 A; V _{GS} = 4.5 V;	-	9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	10		ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	9	-	ns
Source-dra	in diode			•		
V _{SD}	source-drain voltage	$I_S = 2.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.8	1.2	V
	1	1		_	_	_

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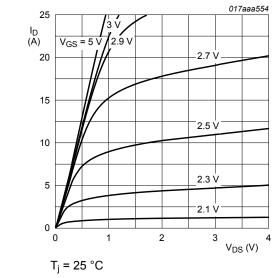


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

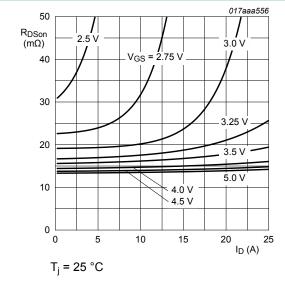


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

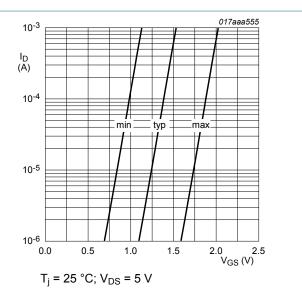


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

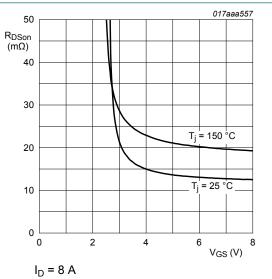


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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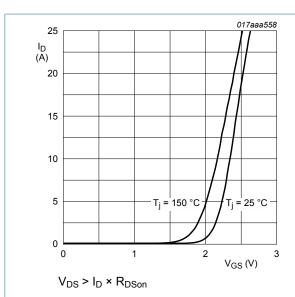


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

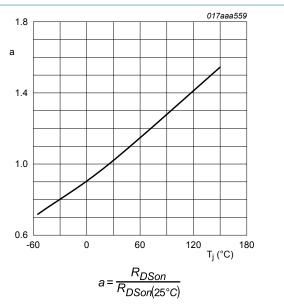


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

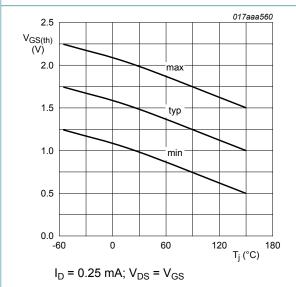


Fig. 12. Gate-source threshold voltage as a function of junction temperature

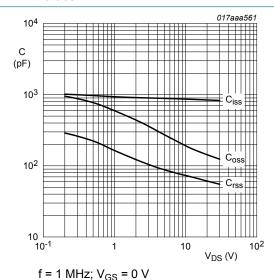


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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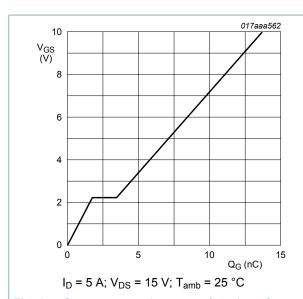


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

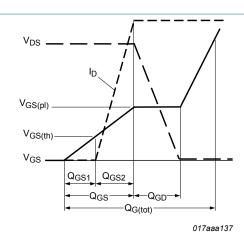


Fig. 15. Gate charge waveform definitions

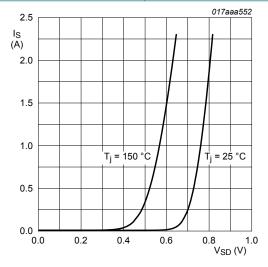
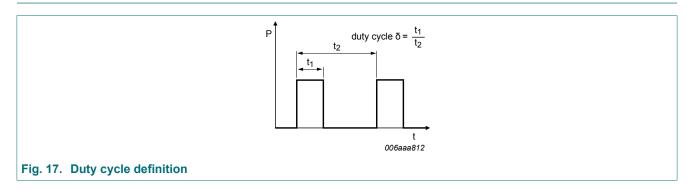


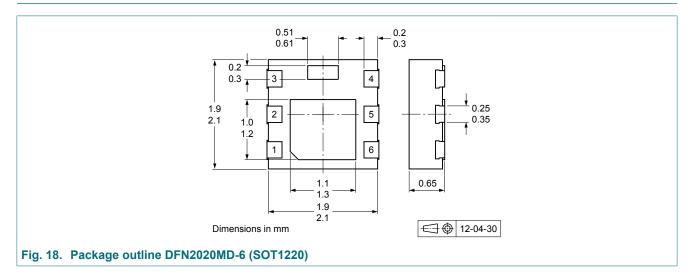
Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information

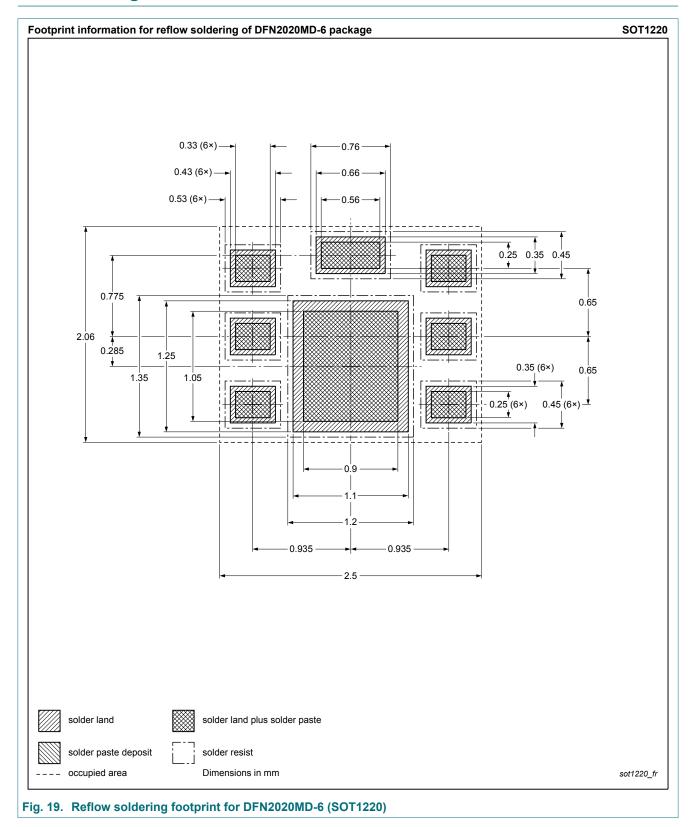


12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMPB11EN v.3	20180712	Product data sheet	-	PMPB11EN v.2			
Modifications:	 Adaption of maximum value of I_{GSS} to minus Adaption of the typical value of g_{fs} according to new wafer fab 						
PMPB11EN v.2	20140114	Product data sheet	-	PMPB11EN v.1			
PMPB11EN v.1	20120516	Product data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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